

P-Type Zinc Oxide Nanowires

Tech ID: 19932 / UC Case 2007-086-0

TECHNOLOGY DESCRIPTION

Researchers at UC San Diego have developed a method of p-doping zinc oxide nanostructures. This wideband gap semiconductor has been difficult to p-dope. The realization of p-doping enables complimentary doping and novel electronic devices, such as transistors, vertical FETs, possibly UV, visible, and white LEDs.

INTELLECTUAL PROPERTY INFO

The method is in early-stage development and is available for licensing. Patents pending.

PATENT STATUS

Country	Type	Number	Dated	Case
United States Of America	Issued Patent	8,426,224	04/23/2013	2007-086

CONTACT

University of California, San Diego
Office of Innovation and Commercialization
innovation@ucsd.edu
tel: 858.534.5815.



OTHER INFORMATION

CATEGORIZED AS

- **Semiconductors**
- Design and Fabrication
- Processing and Production

RELATED CASES

2007-086-0